

2SJ386

Silicon P Channel MOS FET

Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device can be driven from 5 V source
- Suitable for Switching regulator, DC – DC converter

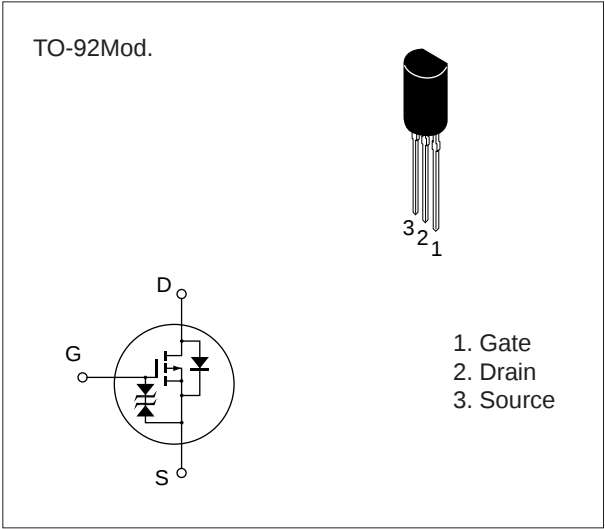


Table 1 Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	−30	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	−3	A
Drain peak current	$I_{D(pulse)}^*$	−5	A
Body–drain diode reverse drain current	I_{DR}	−3	A
Channel dissipation	Pch	0.9	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

* $PW \leq 10 \mu s$, duty cycle $\leq 1 \%$

Table 2 Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-30	—	—	V	$I_D = -10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-10	μA	$V_{DS} = -24 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.5	V	$I_D = -1 \text{ mA}$, $V_{DS} = -10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.3	0.4	Ω	$I_D = -2 \text{ A}$ $V_{GS} = -10 \text{ V}^*$
		—	0.55	0.8	Ω	$I_D = -2 \text{ A}$ $V_{GS} = -4 \text{ V}^*$
Forward transfer admittance	$ y_{fs} $	1.0	1.7	—	S	$I_D = -1 \text{ A}$ $V_{DS} = -10 \text{ V}^*$
Input capacitance	C_{iss}	—	177	—	pF	$V_{DS} = -10 \text{ V}$
Output capacitance	C_{oss}	—	120	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	59	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	8	—	ns	$I_D = -2 \text{ A}$
Rise time	t_r	—	28	—	ns	$V_{GS} = -10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	45	—	ns	$R_L = 15 \text{ }\Omega$
Fall time	t_f	—	60	—	ns	

